

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

- F¹
1. (Withdrawn) A contact structure comprising:
a first substrate;
a second substrate;
a connecting wiring over said first substrate;
a wiring under said second substrate; and
an anisotropic conductive film between the first substrate and the second substrate,
wherein said connecting wiring over said substrate and said wiring under said second substrate are electrically connected by said anisotropic conductive film,
wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film, and
wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film.
 2. (Withdrawn) A contact structure of claim 1 wherein the insulating film is a resin film.
 3. (Withdrawn) The contact structure of claim 1 wherein a thickness of the metallic film is between 100 nm and 1 μ m.
 4. (Withdrawn) A contact structure of claim 1 wherein the metallic film comprises Al.
 5. (Withdrawn) A contact structure of claim 1 wherein the metallic film comprises W.

6. (Withdrawn) A contact structure of claim 1 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

7. (Withdrawn) The contact structure of claim 1 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

8. (Withdrawn) A contact structure of claim 1 wherein the transparent conductive film comprises zinc oxide.

9. (Withdrawn) A contact structure of claim 1 wherein the transparent conductive film comprises zinc oxide and indium oxide.

10. (Withdrawn) A contact structure comprising:
a first substrate;
a second substrate;
a connecting wiring over said first substrate;
a wiring under the second substrate;
an anisotropic conductive film comprising a grain plated with at least one material selected from the group consisting of chromium and gold; and
wherein said connecting wiring over said substrate and said wiring under said second substrate are electrically connected by said anisotropic conductive film,
wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,
wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film, and
wherein said metallic film is not in contact with said grain in said anisotropic conductive film.

11. (Canceled)

F1
Cont.

12. (Withdrawn) The contact structure of claim 10 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

13. (Withdrawn) A contact structure of claim 10 wherein the metallic film comprises Al.

14. (Withdrawn) A contact structure of claim 10 wherein the metallic film comprises W.

15. (Withdrawn) The contact structure of claim 10 wherein the metallic film is a lamination film formed of a W layer and an alloy layer containing W and N.

FI
cont.
16. (Withdrawn) The contact structure of claim 10 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

17. (Withdrawn) A contact structure of claim 10 wherein the transparent conductive film comprises zinc oxide.

18. (Withdrawn) A contact structure of claim 10 wherein the transparent conductive film comprises zinc oxide and indium oxide.

19. (Withdrawn) A semiconductor device comprising:
a circuit comprising a thin film transistor over a substrate; and
a connecting wiring over said substrate for connecting said circuit to another circuit,
wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,
wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film, and
wherein said lamination film has a taper shape.

20. (Withdrawn) A semiconductor device of claim 19 wherein the insulating film is formed from the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

21. (Withdrawn) A semiconductor device of claim 19 wherein the connecting wiring is electrically connected to a wiring of another substrate via an anisotropic conductive film.

22. (Withdrawn) A semiconductor device of claim 19 wherein the insulating film is a resin film.

23. (Withdrawn) A semiconductor device of claim 19 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

24. (Withdrawn) A contact structure of claim 19 wherein the metallic film comprises Al.

25. (Withdrawn) A contact structure of claim 19 wherein the metallic film comprises W.

26. (Withdrawn) A semiconductor device of claim 19 wherein the metallic film is a lamination film formed of a W layer, and a layer comprising W and N.

27. (Withdrawn) A semiconductor device of claim 19 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

28. (Withdrawn) A contact structure of claim 19 wherein the transparent conductive film comprises zinc oxide.

29. (Withdrawn) A contact structure of claim 19 wherein the transparent conductive film comprises zinc oxide and indium oxide.

F-1
Cont.

30. (Withdrawn) The device of claim 19 wherein said semiconductor device is one of a liquid crystal device and EL display device.

FI
cont.

31. (Currently Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing to said first substrate;
a connecting wiring comprising a metallic film and a transparent conductive film ~~in contact with~~ over said metallic film for connecting said circuit to another circuit; and
an insulating film ~~in contact with~~ covering a side surface of said metallic film, wherein said connecting wiring and said insulating film are formed over said first substrate,
wherein said insulating film is formed along with the length-direction a longer side and the width-direction a shorter side of said ~~lamination~~ metallic film, and wherein said ~~connecting wiring~~ metallic film has a taper shape.

32. (Currently Amended) A semiconductor device of claim 31 wherein the insulating film ~~is formed of~~ comprises the same ~~materials~~ material as that of contained in an insulating film between a gate wiring and a source wiring of the thin film transistor.

33. (Previously Presented) A semiconductor device of claim 31 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

34. (Canceled)

35. (Previously Presented) A semiconductor device of claim 31 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

36. (Previously Presented) A semiconductor device of claim 31 wherein the metallic film comprises Al.

37. (Previously Presented) A semiconductor device of claim 31 wherein the metallic film comprises W.

38. (Currently Amended) A semiconductor device of claim 31 wherein the metallic film is a lamination film ~~formed of~~ comprising a W layer and a layer comprising W and N.

FI
cont. 39. (Previously Presented) A semiconductor device of claim 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

40. (Previously Presented) A semiconductor device of claim 31 wherein the transparent conductive film comprises zinc oxide.

41. (Previously Presented) A semiconductor device of claim 31 wherein the transparent conductive film comprises zinc oxide and indium oxide.

42. (Original) The device of claim 31 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

43. (Currently Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing to said first substrate;
a connecting wiring comprising a metallic film and a transparent conductive film ~~in contact with~~ over said metallic film for connecting said circuit to another circuit;
a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and
an insulating film ~~in contact with~~ covering a side surface of said metallic film comprising the same material as that of the column-shape spacer,
wherein said connecting wiring, said column spacer, and said ~~protecting~~ insulating film are formed over said first substrate,

wherein said insulating film is formed along with [the length direction] a longer side and ~~the width direction~~ a shorter side of said lamination metallic film, and wherein said ~~connecting wiring~~ metallic film has a taper shape.

44. (Previously Presented) A semiconductor device of claim 43 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

45. (Canceled)

46. (Previously Presented) A semiconductor device of claim 43 wherein a thickness of the metallic film is between 100 nm and 1 μm .

FI
Cont. 47. (Previously Presented) A semiconductor device of claim 43 wherein the metallic film comprises Al.

48. (Previously Presented) A semiconductor device of claim 43 wherein the metallic film comprises W.

49. (Currently Amended) A semiconductor device of claim 43 wherein the metallic film is a lamination film ~~formed of~~ comprising a W layer and a layer comprising W and N.

50. (Previously Presented) A semiconductor device of claim 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

51. (Previously Presented) A semiconductor device of claim 43 wherein the transparent conductive film comprises zinc oxide.

52. (Previously Presented) A semiconductor device of claim 43 wherein the transparent conductive film comprises zinc oxide and indium oxide.

53. (Original) The device of claim 43 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

54. (Withdrawn) A semiconductor device of claim 19 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

FI 55. (Currently Amended) A semiconductor device of claim 31 wherein the ~~lamination film~~ connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

56. (Currently Amended) A semiconductor device of claim 43 wherein the ~~lamination film~~ connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.
